



SHEET 1 OF 1

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

241807US2DIV

SERIAL NO.

10/657,068

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Toshiaki IWAMATSU, et al.

FILING DATE

September 9, 2003

GROUP

2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
ah	AO	1997-0051968	07/29/1997	KOREA (with English extract)		X
ah	AP	1998-058455	10/07/1998	KOREA (with English extract)		X
ah	AQ	1996-0002744	01/26/1996	KOREA (with English extract)		X
	AR					
	AS					
	AT					
	AU					
	AV					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	
	AX	
	AY	
	AZ	

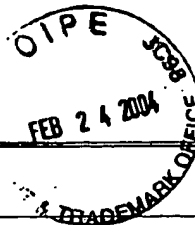
☐ Additional References sheet(s) attached

Examiner

Date Considered

10/16/03

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241807US2DIV		SERIAL NO. 10/657,068	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Toshiaki IWAMATSU, et al.			
				FILING DATE September 9, 2003		GROUP 2812	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AL	AA	4,682,403	07/28/1987	J. HARTMANN, et al.			
	AB	5,847,433	12/08/1998	M. KERBER			
	AC	4,422,885	12/27/1983	R. W. BROWER, et al.			
	AD	4,498,223	02/12/1985	E. A. GOLDMAN, et al.			
	AE	5,841,185	11/24/1998	A. ISHIKAWA			
	AF	5,164,803	11/17/1992	H. OZAKI, et al.			
	AG	5,086,012	02/04/1992	S. K. SIK			
	AH						
	AI						
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AL							
AM							
AN							
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW						
	AX						
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner <i>Andy Murray</i>					Date Considered 10/16/04		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. <b>241807US2DIV</b>		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Toshiaki IWAMATSU et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AK	AA	6,261,882	07/2001	Kim			
	AB	6,097,103	08/2000	Ishigaki			
	AC	5,956,617	09/1999	Kimura et al.			
	AD	5,612,243	03/1997	Verrett			
	AE	5,294,822	03/1994	Verrett			
	AF	5,223,456	06/1993	Malwah			
	AG	4,786,611	11/1988	Pfiester			
	AH	4,476,482	10/1984	Scott et al.			
	AI	4,374,700	02/1983	Scott et al.			
	AJ						
AK							
AL							
AM							
AN							
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
AK	AO	2-159035	06/19/90	JAPAN (w/ English Extract)			X
	AP	9-275134	10/21/97	JAPAN (w/ English Extract)			X
	AQ	6-204334	07/22/94	JAPAN (w/ English Extract)			X
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
AK	AW	M. INOHARA, et al., "Copper Contamination Induced Degradation of MOSFET Characteristics and Reliability", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 26-27					
	AX	Kazuyuki HOZAWA, et al., "Copper distribution behavior near a SiO <sub>2</sub> /Si interface by low-temperature (<400°C) annealing and its influence on electrical characteristics of MOS-capacitors", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 24-25					
	AY	A. STEEGEN, et al., "Silicide and Shallow Trench Isolation line width dependent stress induced junction leakage", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 180-181					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>Andy K...</i>					Date Considered 10/16/04		
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